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NPN/NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 47 kΩ

Rev. 5 — 12 November 2013

**Product data sheet** 

### 1. Product profile

#### **1.1 General description**

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview
	i i oaaot	010111011

Type number	Package		PNP/PNP	NPN/PNP	Package
	NXP	JEITA	complement	complement	configuration
PEMH9	SOT666	-	PEMB9	PEMD9	ultra small and flat lead
PIMH9	SOT457	SC-74	-	-	small
PUMH9	SOT363	SC-88	PUMB9	PUMD9	very small

#### **1.2 Features and benefits**

- 100 mA output current capability
   Reduces component count
- Built-in bias resistors
- Simplifies circuit design

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	



- Reduces pick and place costs
- AEC-Q101 qualified

### NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

### 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

# 3. Ordering information

Table 4.	Ordering information	
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Type number	Package					
	Name	Description	Version			
PEMH9	-	plastic surface-mounted package; 6 leads	SOT666			
PIMH9	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457			
PUMH9	SC-88	plastic surface-mounted package; 6 leads	SOT363			

# 4. Marking

#### Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMH9	Н9
PIMH9	Н9
PUMH9	H*9

[1] \* = placeholder for manufacturing site code

| | 2 3 *sym063* 

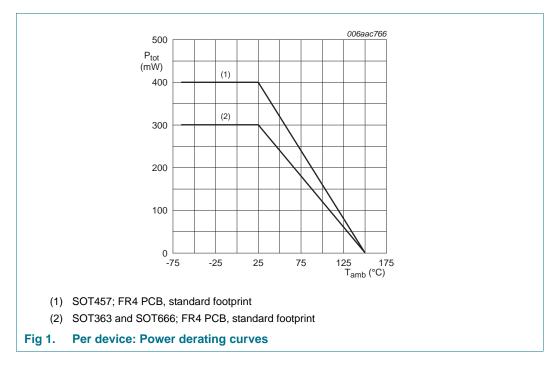
### NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

### 5. Limiting values

Symbol	Parameter	Conditions	Min	Мах	Unit
Per transis	stor				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-6	V
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH9 (SOT666)		<u>[1]</u> -	200	mW
	PIMH9 (SOT457)		<u>[1]</u>	250	mW
	PUMH9 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH9 (SOT666)		<u>[1]</u> _	300	mW
	PIMH9 (SOT457)		<u>[1]</u>	400	mW
	PUMH9 (SOT363)		<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



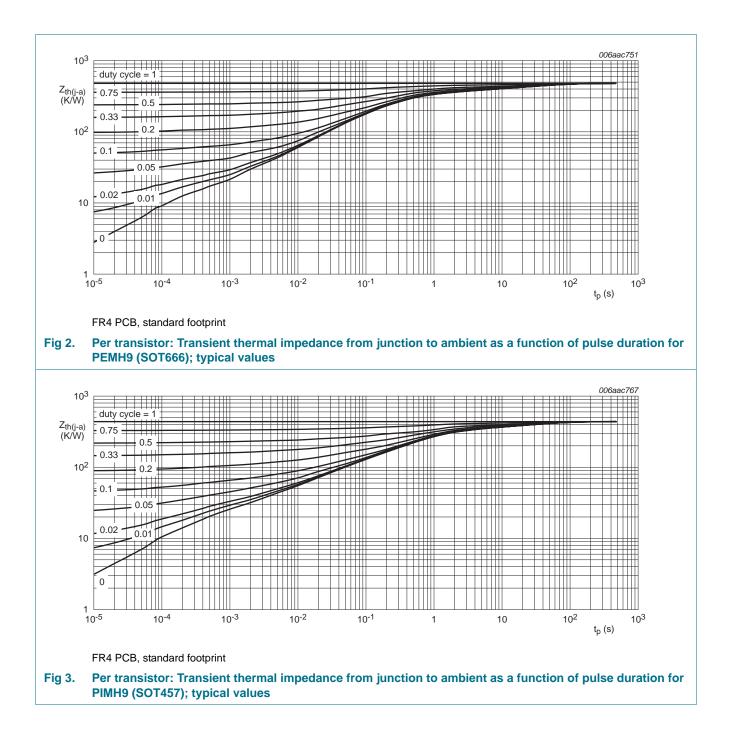
### 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PEMH9 (SOT666)		<u>[1]</u> -	-	625	K/W
	PIMH9 (SOT457)		<u>[1]</u> -	-	500	K/W
	PUMH9 (SOT363)		<u>[1]</u> -	-	625	K/W
Per device	;					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PEMH9 (SOT666)		<u>[1]</u> -	-	417	K/W
	PIMH9 (SOT457)		<u>[1]</u> -	-	313	K/W
	PUMH9 (SOT363)		<u>[1]</u> -	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

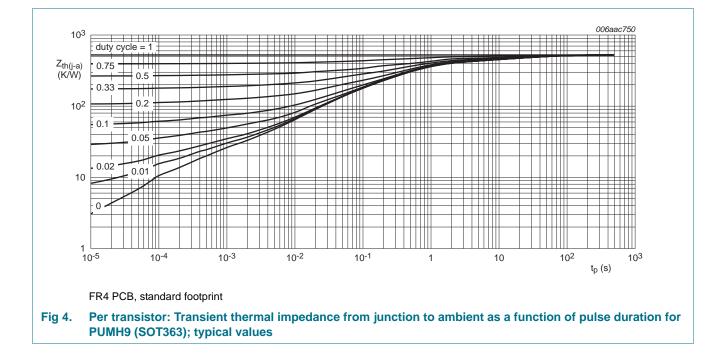
# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

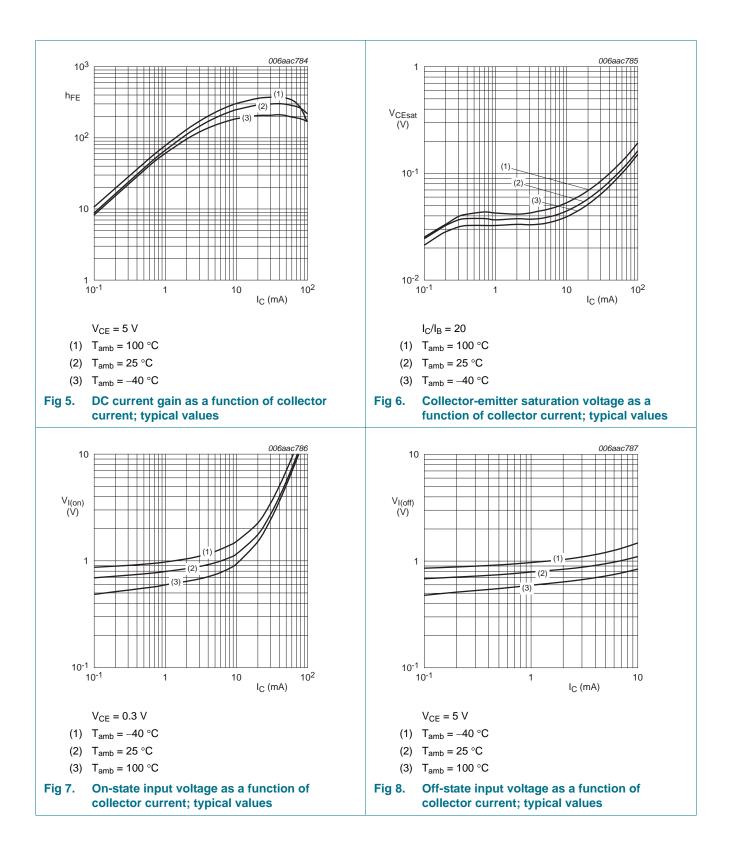
# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	150	μA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = 5 V; $I_C$ = 100 $\mu$ A	-	0.7	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}$	1.4	0.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_C = 10 \text{ mA};$ f = 100 MHz	<u>1]</u> _	230	-	MHz

[1] Characteristics of built-in transistor

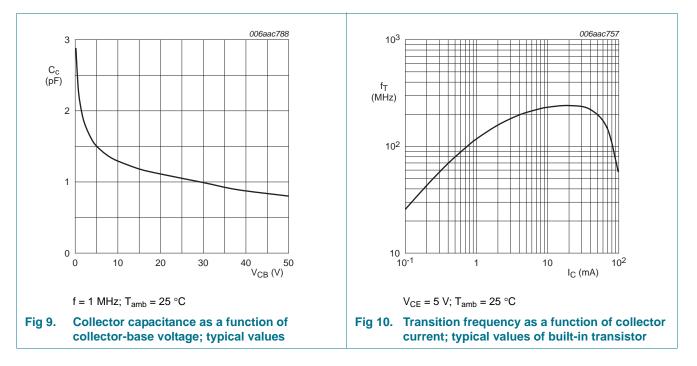
# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



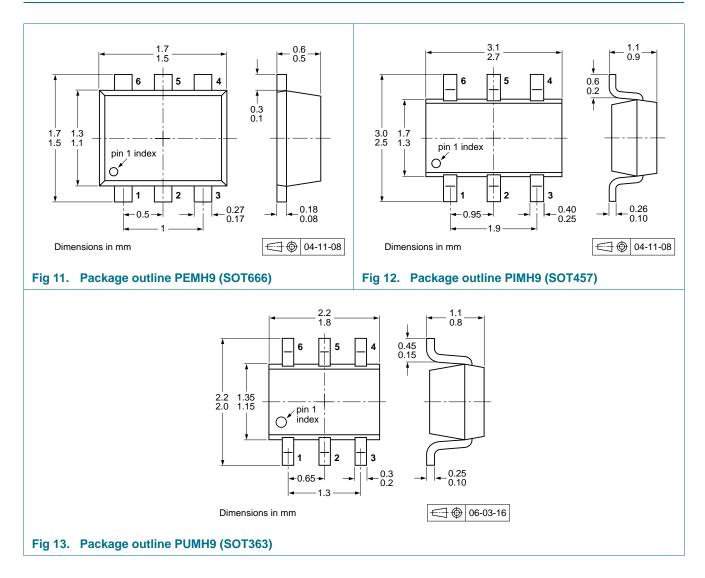
### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

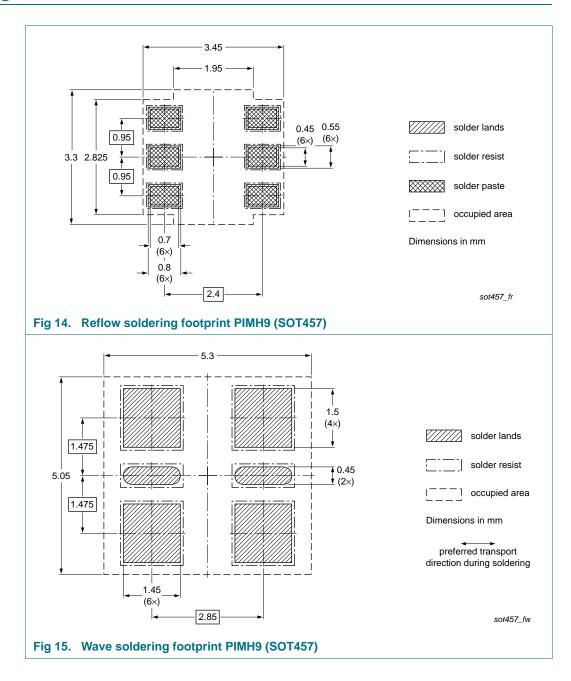
NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

# 9. Package outline

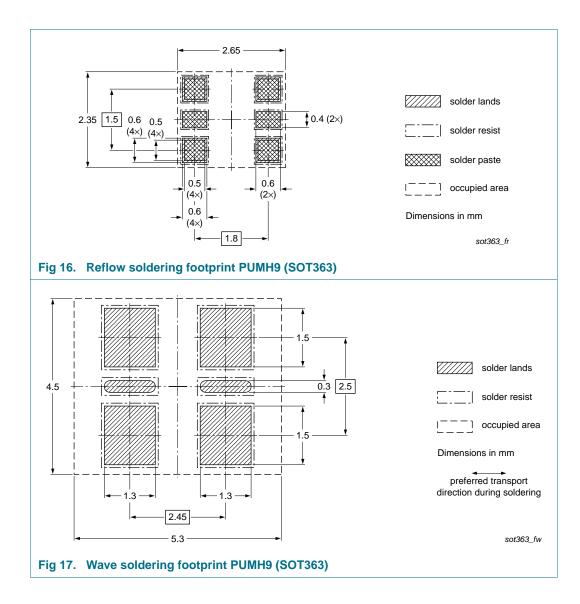


NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

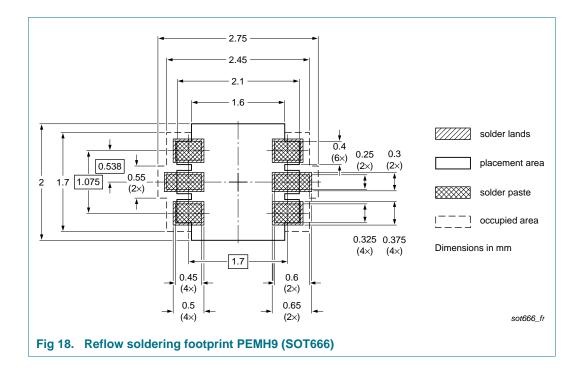
### **10. Soldering**



NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 



# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

# **11. Revision history**

Table 9. Revision histor	у			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH9_PIMH9_PUMH9 v.	5 20131112	Product data sheet	-	PIMH9_PUMH9_PEMH9 v.4
Modifications:		of this document has been r of NXP Semiconductors.	edesigned to c	omply with the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the ne	ew company na	ame where appropriate.
	Section 1 "F	Product profile": updated		
	Section 4 "I	Marking": updated		
	• Figure 1 to	<u>10</u> : added		
	Section 5 "L	<u>_imiting values"</u> : updated		
	Section 6 "	Thermal characteristics": upo	lated	
	<ul> <li>Table 8 "Ch</li> </ul>	aracteristics": Vi(on) redefine	d to V <sub>I(on)</sub> on-st	ate input voltage, V <sub>i(off)</sub> redefined
	to V <sub>I(off)</sub> off-	state input voltage, I <sub>CEO</sub> upd	ated, $f_T$ added	
	<ul> <li>Section 8 "</li> </ul>	Test information": added		
	<ul> <li>Section 9 "F</li> </ul>	Package outline": supersede	d by minimized	l package outline drawings
	Section 10	"Soldering": added		
	Section 12	"Legal information": updated		
PIMH9_PUMH9_PEMH9 v.4	4 20040414	Product data sheet	-	PIMH9_PUMH9_PEMH9 v.3
PIMH9_PUMH9_PEMH9 v.3	3 20030915	Product specification		-

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

### **12. Legal information**

#### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PEMH9; PIMH9; PUMH9

#### NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

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# PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

### 14. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 7
8	Test information 9
8.1	Quality information 9
9	Package outline 10
10	Soldering 11
11	Revision history 14
12	Legal information 15
12.1	Data sheet status 15
12.2	Definitions 15
12.3	Disclaimers
12.4	Trademarks 16
13	Contact information 16
14	Contents 17

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Date of release: 12 November 2013 Document identifier: PEMH9\_PIMH9\_PUMH9

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